Invited Journal Articles


Refereed Journal Articles


**Invited Conference Presentations**


10. H.-S. P. Wong, “Memory – the N3XT Frontier,” invited keynote paper, 8th Annual Non-Volatile Memories Workshop (NVMW 2017), La Jolla, CA March 12-14, 2017


15. Yoshio Nishi, “Recent progress in physics and technology of oxide based resistive switching memory”, *IEEE Silicon Valley Nanoelectronics Workshop*, June, 2015, Santa Clara, CA

16. Y. Nishi, “Emerging Nonvolatile Memory Devices “, JSPS anniversary international workshop, November 5, 2015, Univ. Tokyo, Japan


26. Blanka Magyari-Kope and Y. Nishi, “Modeling aspects of forming and switching in RRAM devices, including possible doping effects forimproved characteristics”, NCCAVS Thin Film Users Group (TFUG) ”Advanced Memory Meeting”, November 2013, San Jose, USA


40. Y. Wu, J. Liang, S. Yu, X. Guan, and H.-S. P. Wong, "Resistive switching random access memory - materials, device, interconnects, and scaling considerations", invited
talk, IEEE International Integrated Reliability Workshop (IIRW), October 14-18, 2012, Fallen Leaf Lake, CA, USA.


Contributed Conference Presentations


